Abstract of the Disclosure

The preferred embodiments described herein relate to a method and system for temperature compensation for memory cells with temperature-dependent behavior. In one preferred embodiment, at least one of a first temperature-dependent reference voltage comprising a negative temperature coefficient and a second temperature-dependent reference voltage comprising a positive temperature coefficient is generated. One of a wordline voltage and a bitline voltage is generated from one of the at least one of the first and second temperature-dependent reference voltages. The other of the wordline and bitline voltages is generated, and the wordline and bitline voltages are applied across a memory cell. Other methods and systems are disclosed for sensing a memory cell comprising temperature-dependent behavior, and each of the preferred embodiments can be used alone or in combination with one another.